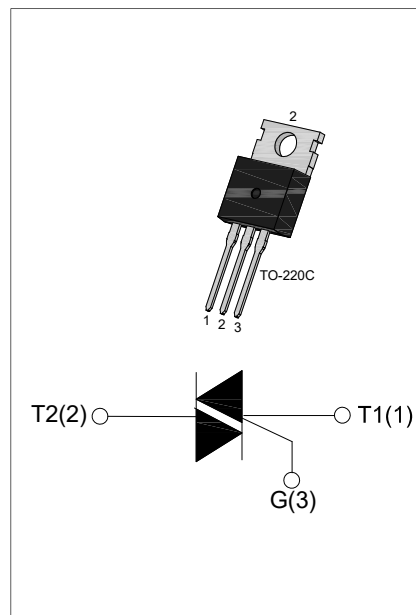


**DESCRIPTION:**

With high ability to withstand the shock loading of large current, JST16C-800SW triac provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, especially recommended for use on inductive load. Complying with UL standards (File ref: E252906). Package TO-220C is RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	800	V

**ABSOLUTE MAXIMUM RATINGS**

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	°C
Operating junction temperature range		T_j	-40-125	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}\text{C}$)		V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}\text{C}$)		V_{RRM}	800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-220C ($T_C=107^{\circ}\text{C}$)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)		I_{TSM}	160	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	128	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di/dt	100	$\text{A}/\mu\text{s}$
Peak gate current $t_p=20\mu\text{s}$		I_{GM}	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power $t_p=20\mu\text{s}$		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX	10	mA
V_{GT}		I - II -III	MAX	1.3	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	30	mA
		II		40	
I_H	$I_T=100\text{mA}$		MAX	25	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}\text{C}$		MIN	200	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=22.5\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^{\circ}\text{C}$	0.93	V
R_d	Dynamic resistance	$T_j=125^{\circ}\text{C}$	26	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=125^{\circ}\text{C}$	1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220C	1.2	$^{\circ}\text{C}/\text{W}$

ORDERING INFORMATION

J	ST	16	C	-800	SW	-/
JieJie Microelectronics Co.,Ltd	Triacs	$I_{T(RMS)}: 16A$	C:TO-220C	800: $V_{DRM} / V_{RRM} \geq 800V$	CW: $I_{GT1-3} \leq 10mA$	Blank: Tube

MARKING

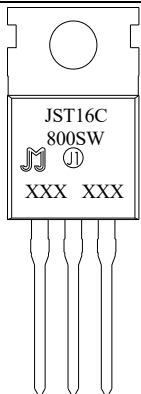
 JST16C 800SW XXX XXX	XXX XXX Year Month Production Code
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FIG.1: Maximum power dissipation versus RMS on-state current

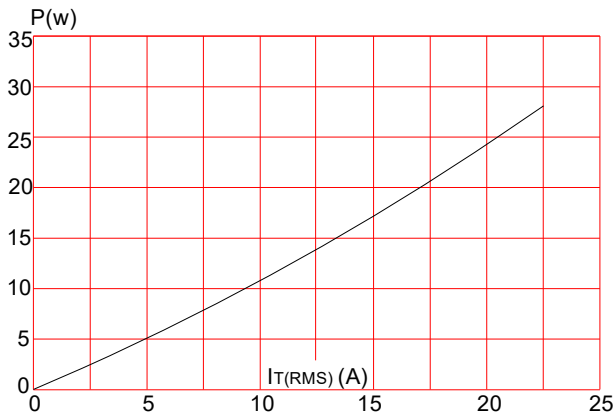


FIG.3: Surge peak on-state current versus number of cycles

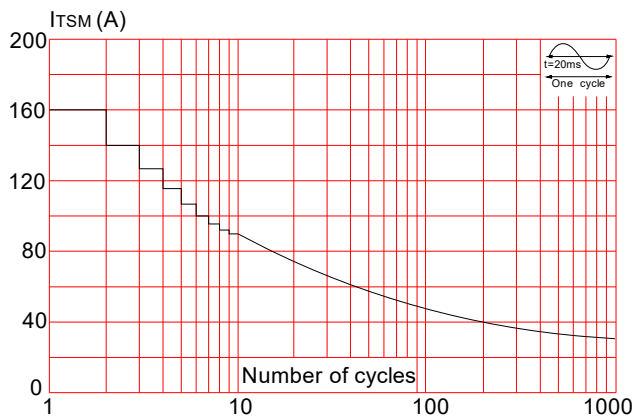


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

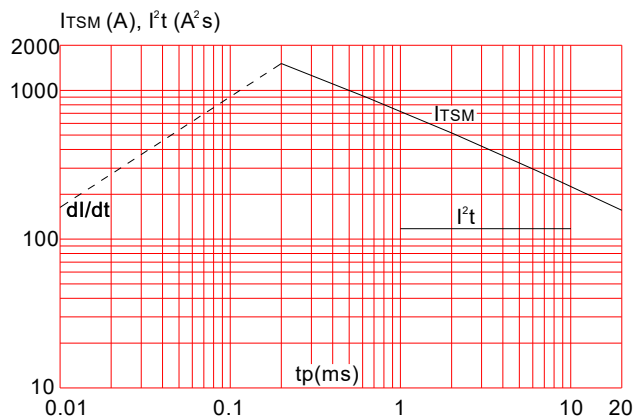


FIG.2: RMS on-state current versus case temperature

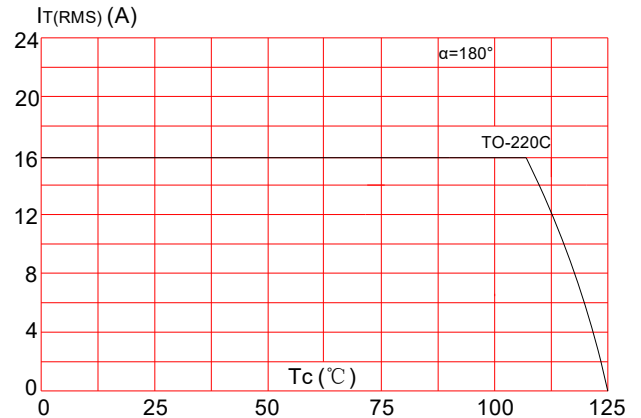


FIG.4: On-state characteristics (maximum values)

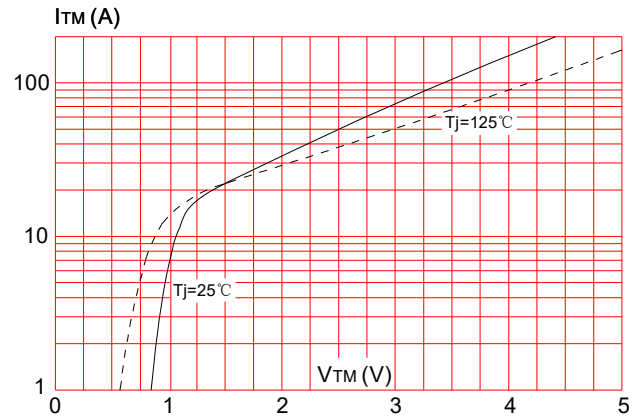
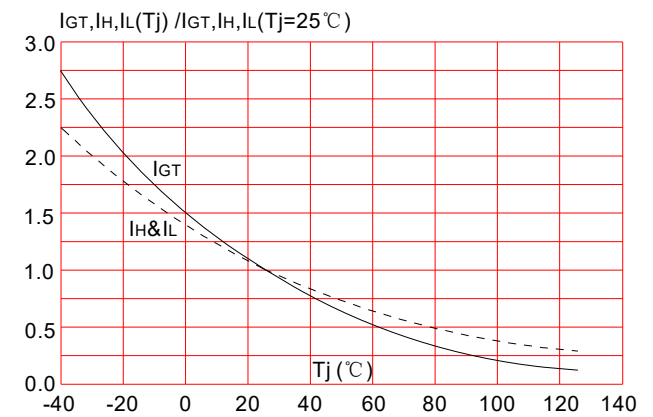


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



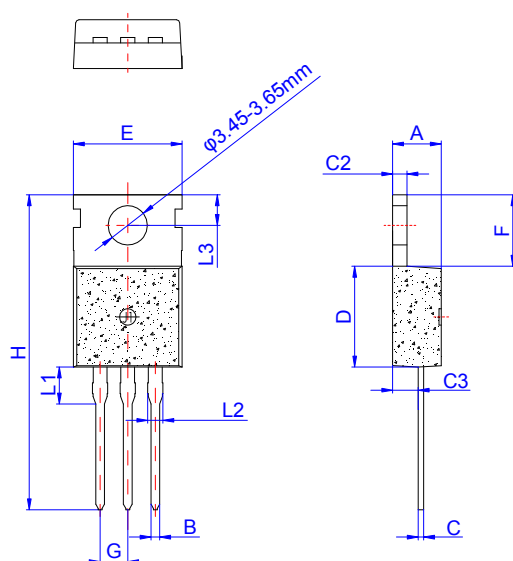
ORDERING INFORMATION

Order code	Voltage $V_{\text{DRM}}/V_{\text{RRM}}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST16C-800SW	800	10	TO-220C	50	Tube

Document Revision History

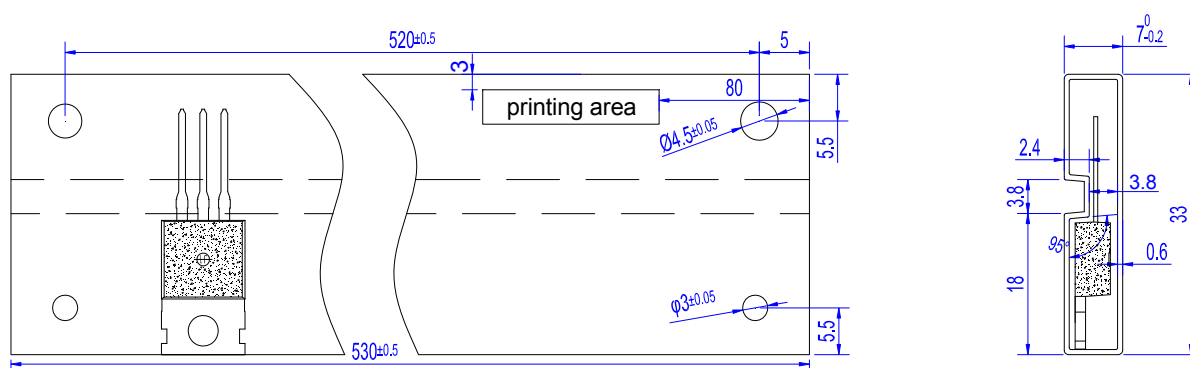
Date	Revision	Changes
Mar 21, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.23		1.32	0.048		0.052
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.39			0.133	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220C	TUBE	50	1,000	5,000



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